TOSHIBA Photocoupler GaAs Ired & Photo-Triac

# TLP363J

Triac Drivers Programmable Controllers AC-Output Modules Solid State Relays

The TOSHIBA TLP363J consists of a zero-voltage-crossing turn-on

photo-triac optically coupled to a gallium arsenide infrared-emitting diode in a four-lead plastic DIP package.

This product has a greater capacity to withstand external noise than the TLP361J.

- Peak off-state voltage: 600 V (Min.)
- Trigger LED current: 10 mA (Max.)
- On-state current: 100 mA (Max.)
- Isolation voltage: 5000 Vrms (Min.)
- Zero crossing function
- UL recognized: UL1577, file No. E67349
- Option (D4) type

TÜV approved: DIN EN60747-5-2

Certificate No. R50033433

Maximum operating insulation voltage 390 Vpk

Maximum permissible overvoltage : 8000 Vpk

(Note) When an EN60747-5-2 approved type is needed, please designate "Option (D4)."

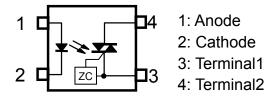
#### ·Construction mechanical rating

	7.62 mm pitch TLPXXX type	10.16 mm pitch TLPXXX type		
Creepage distance	7.0 mm (min)	8.0 mm (min)		
Clearance	7.0 mm (min)	8.0 mm (min)		
Insulation thickness	0.4 mm (min)	0.4 mm (min)		

#### •Trigger LED Current

Classi-	Trigger LED	Marking of	
fication*	V <sub>T</sub> = 3 V,	classification	
	Min.	Max.	classification
Standard	-	10	blank

#### Pin Configuration (top view)



(Note) When specifying the application type name for certification testing, be sure to use the standard product type name, e.g.,

TLP363J

 $7.62 \pm 0.25$ 

0.25

7.85~8.80

11-5B2

 $6.4 \pm 0.25$ 

 $3.65^{+}$ 

0.8±0.

min

2.51

 $4.58 \pm 0.25$ 

 $2.54 \pm 0.25$ 

Weight: 0.26 g (Typ.)

1.2±0.1

 $0.5 \pm 0.1$ 

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#### Absolute Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
Forward current			١ <sub>F</sub>	50	mA	
	Forward current derating (Ta ≥ 53°C)		∆l <sub>F</sub> /°C	-0.7	mA /°C	
LED	Peak forward current (100 µs pulse, 100 pps)		I <sub>FP</sub>	1	А	
	Reverse voltage		VR	5	V	
	Junction temperature		Тj	125	°C	
Off-state output terminal voltage				600	V	
	On-state RMS current	Ta = 25°C		100	mA	
ъ		Ta = 70°C	I <sub>T(RMS)</sub>	50		
Detector	On-state current derating (Ta ≥ 25°C)	∆I <sub>T</sub> /°C	-1.1	mA /°C		
ŏ	Peak on-state current (100 µs pulse, 120 pps)	I <sub>TP</sub>	2	А		
	Peak nonrepetitive surge current (Pw =10 ms, DC = 10%)			1.2	А	
	Junction temperature	Тj	115	°C		
Stor	Storage temperature range			-55~125	°C	
Operating temperature range			T <sub>opr</sub>	-40~100	°C	
Lead soldering temperature (10 s)			T <sub>sol</sub>	260	°C	
Isola	Isolation voltage (AC,1min. , R.H. ≤ 60%) (Note 1)			5000	Vrms	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1): Pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>AC</sub>	—	—	240	Vac
Forward current	١ <sub>F</sub>	15	20	25	mA
Peak on-state current	I <sub>TP</sub>	—	_	1	А
Operating temperature	T <sub>opr</sub>	-25		85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

## **Electrical Characteristics (Ta = 25°C)**

	Characteristic	Symbol	Test Condition		Тур.	Max.	Unit
	Forward Voltage	VF	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5 V		—	10	μA
	Capacitance	CT	V = 0, f = 1 MHz		30	_	pF
	Peak off-state current	I <sub>DRM</sub>	V <sub>DRM</sub> = 600 V		10	1000	nA
<u>ـ</u>	Peak on-state voltage	V <sub>TM</sub>	I <sub>TM</sub> = 100 mA		1.7	3.0	V
Detector	Holding current	Ι <sub>Η</sub>	_		0.6	_	mA
Det	Critical rate of rise of off-state voltage	dv/dt	Vin = 240 Vrms , Ta = 85°C (Note 2)	200	500	_	V/µs
	Critical rate of rise of commutating voltage	dv/dt(c)	Vin = 60 Vrms , I <sub>T</sub> = 15 mA (Note 2)	_	0.2	_	V/µs

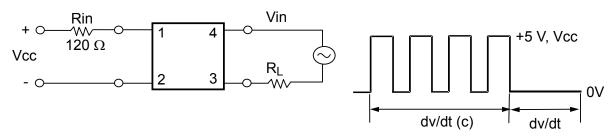
### Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I <sub>FT</sub>	V <sub>T</sub> = 3 V	_	_	10	mA
Inhibit voltage	VIH	I <sub>F</sub> = Rated I <sub>FT</sub>	_	_	20	V
Leakage in inhibited state	Ιн	I <sub>F</sub> = Rated I <sub>FT</sub> V <sub>T =</sub> Rated V <sub>DRM</sub>	_	200	600	μΑ
Turn-on time	t <sub>ON</sub>	$V_D = 3 \rightarrow 1.5 \text{ V}$ , $R_L = 20 \Omega$ I <sub>F</sub> = Rated I <sub>FT</sub> X1.5	_	30	100	μs
Impulse noise durability	V <sub>N</sub>	t <sub>N</sub> =1μs, Snuber condition 100 Ω +0.033 μF (Note.3)		2000		V

## Isolation Characteristics (Ta = 25°C)

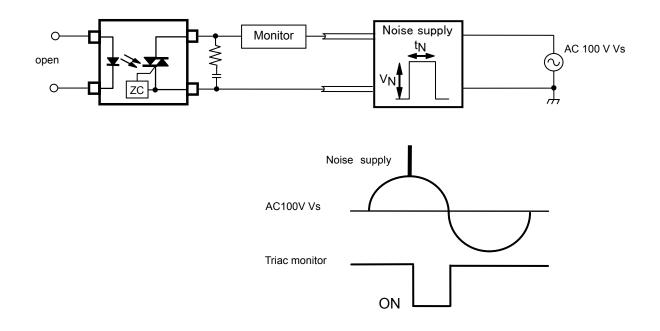
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	CS	V <sub>S</sub> = 0 , f = 1 MHz	—	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H.≤ 60%	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage	BVS	AC , 1 minute	5000	_	_	Vrms
		AC , 1 second, in oil	_	10000	_	vinis
		DC , 1 minute, in oil	_	10000	_	Vdc

#### (Note 2): dv/dt test circuit

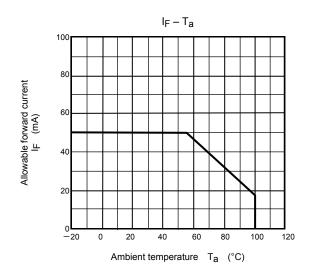


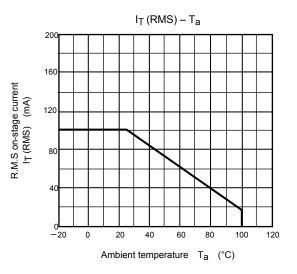
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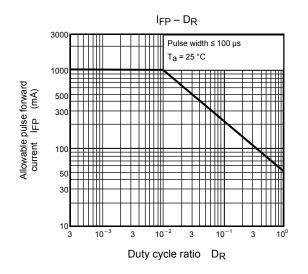
## (Note 3): impulse noise durability test circuit

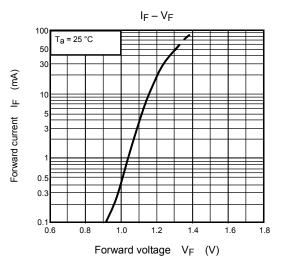


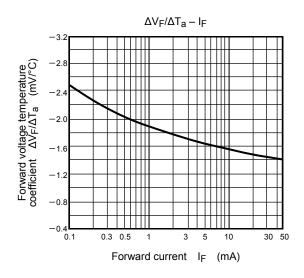
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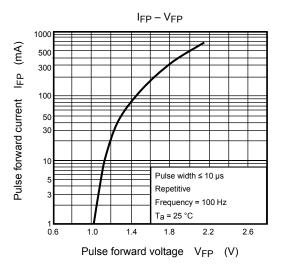




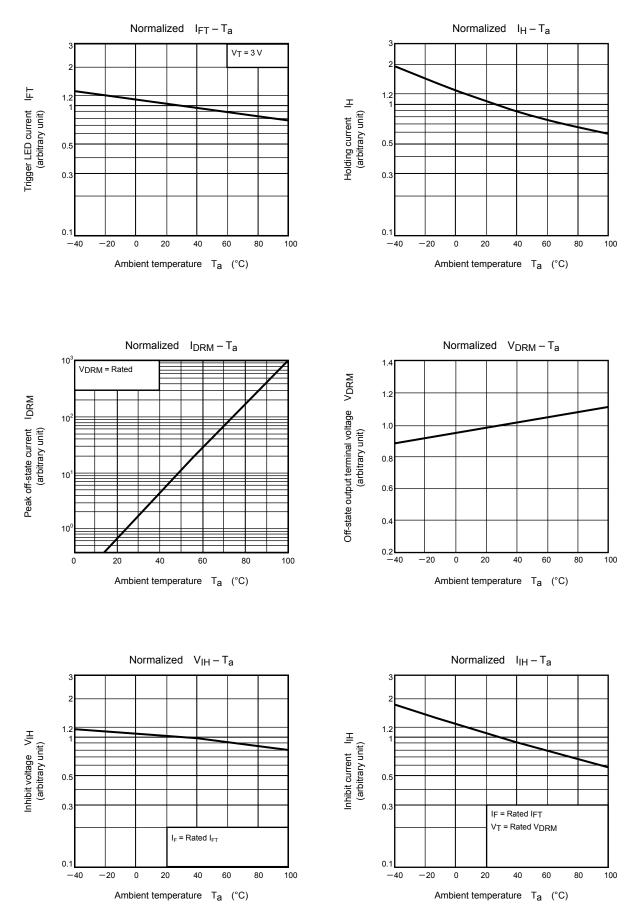




\*: The above graphs show typical characteristics.



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\*: The above graphs show typical characteristics.

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